

D. Thin Film Process Technology 분과

Room F

창의관 (B114)

일 시 : 2월 17일(금) 11:20-12:35

세션명 : [FF2-D] Thin Film Deposition

좌 장 : 윤성민(경희대학교), 김형섭(성균관대학교)

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- FF2-D-1 11:20-11:50 **[Invited] Nonvolatile Memory Technology with Engineered Tunnel Barriers Based on High-k Materials**
저자: Won-Ju Cho
소속: Department of Electronic Materials Engineering, Kwangwoon University
- FF2-D-2 11:50-12:05 **Atomic Layer Deposition of (GeTe₂)_{1-x}(Sb₂Te₃)_x Film for Phase Change Memory**
저자: Taeyong Eom¹, Seol Choi¹, Byung Joon Choi¹, Min Hwan Lee¹, Taehong Gwon¹, Sang Ho Rha¹, Woongkyu Lee¹, Moo-Sung Kim², Manchao Xiao³, and Cheol Seong Hwang¹
소속: ¹WCU Hybrid Material Program, Department of Materials Science and Engineering, Seoul National University, and Inter-university Semiconductor Research Center, Seoul National University, ²Air Products Korea, ³Air Products and Chemicals, Inc.
- FF2-D-3 12:05-12:20 **Atomic Layer Deposition of SrTiO₃ Films with Cp-based Precursors**
저자: Woongkyu Lee, Jeong Hwan Han, Woojin Jeon, and Cheol Seong Hwang
소속: WCU Hybrid Materials Program, Department of Materials Science and Engineering and Inter-university Semiconductor Research Center, Seoul National University
- FF2-D-4 12:20-12:35 **Investigation on Suppression of Nickel-Silicide Formation by Fluorocarbon Reactive Ion Etch (RIE) and Plasma-Enhanced Deposition**
저자: Hyun Woo Kim¹, Jung Han Lee¹, Min-Chul Sun^{1,2}, and Byung-Gook Park¹
소속: ¹ Inter-University Semiconductor Research Center (ISRC) and

School of Electrical Engineering and Computer Science, Seoul
National University, ²TD Team (S. LSI), Semiconductor
Business Group, Samsung Electronics Co., Ltd.

**FF2-D-5 12:35-12:50 Comparative Study of Ultralow-k pSiCOH (k=2.5) Films by using
Different C-bridged Si-precursors**

저자: Gyeonghee Kim¹, Sang Hoon Ahn¹, Insun Jung², Kyu-Hee Han¹,
Janghee Lee¹, Jongho Yun¹, Gil Heyun Choi¹, Ho Kyu Kang¹,
and Chillhee Chung¹

소속: ¹Process Development Team, Semiconductor R&D Center,
Samsung Electronics Co., Ltd., ²Analytical Engineering Group,
AE Center, Samsung Advanced Institute of Technology